CLAIMS

- 1. An apparatus, comprising:
- a) a two-part pad, comprising
 - i) a first pad, which is rectangular,metallic, about 50 microns x 50 microns, andabout 1 micron thick; and
 - ii) a second pad, which is rectangular, metallic, about 30 x 30 microns, about 1 micron thick, and having one edge coinciding with part of an edge of the first pad; and
- c) a semiconductor substrate supporting the two-part pad.
- 2. Apparatus according to claim 1, wherein damage occurring to the first pad does not inhibit wetting of solder to the second pad.
- 3. Apparatus according to claim 1, and further comprising electronic circuitry supported by the semiconductor substrate, and a trace connecting to the two-part pad.
- 4. Apparatus according to claim 3, wherein damage occurring to the first pad as a result of testing of the electronic circuitry does not inhibit wetting of solder to the second pad.

- 5. A method, comprising:
- a) on a semiconductor substrate, constructing a pad which connects to a trace, the pad containing
 - i) a body, and
 - ii) a head electrically connected to the
 body;
- b) communicating with the trace by applying a probe to the body; and
- c) connecting an external component to the trace by flip-chip bonding to the head.
- 6. Method according to claim 5, wherein the probe is not applied to the head.
- 7. Method according to claim 5, wherein the flip-chip bonding does not involve the body.
- 8. Method according to claim 5, wherein the probe is not applied to the head, and the flip-chip bonding does not involve the body.
 - An apparatus, comprising:
 - a) a die containing one, or more, integrated circuits;
 - b) on a surface of the die, a metallic pad having

- i) a first region bearing a fused material which connects to a second pad; and
- ii) a second region lacking fused material.
- 10. Apparatus according to claim 9, wherein the first region has an area less than 1600 square microns, and the second region has an area greater than 1600 square microns.
- 11. Apparatus according to claim 9, wherein the first and second regions are generally rectangular in shape, and share a common border.
- 12. Apparatus according to claim 9, wherein the die comprises crystalline silicon, the integrated circuit comprises a driver for lasers, and further comprising:
 - c) a second die, containing
 - i) lasers, and
 - ii) a pad connecting to said fused material.
 - 13. Apparatus, comprising:
 - a) a first array of metallic pads A, supported by a first substrate;
 - b) a second array of metallic pads B, supported by a second substrate, each pad B connected to a respective pad A by a solder bond;

- c) a third array of metallic pads C, each pad C supported by the first substrate and electrically connected to a respective pad A;
- d) a control circuit which delivers signals to the pads
 A; and
- e) an array of optoelectronic devices, each connected to a respective pad B.
- 14. Apparatus according to claim 13, and further comprising
- f) a fourth array of metallic pads D, each pad D supported by the second substrate and electrically connected to a respective pad B.
- 15. Apparatus according to claim 13, wherein each pad B is about 30 \times 30 microns, and 1 micron thick.
- 16. Apparatus according to claim 13, wherein each pad C is about 30 \times 30 microns, and 1 micron thick.
- 17. Apparatus according to claim 16, wherein each pad C is separated from its neighbor by about 100 microns.